

# Low Power, Low Noise Operational Amplifiers

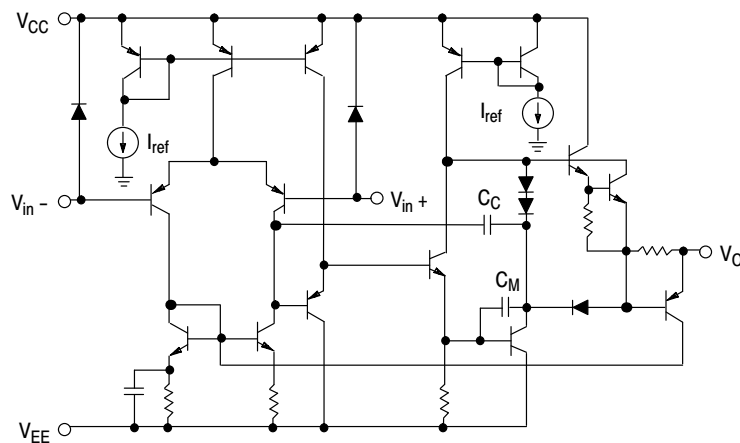
## MC33178, MC33179

The MC33178/9 series is a family of high quality monolithic amplifiers employing Bipolar technology with innovative high performance concepts for quality audio and data signal processing applications. This device family incorporates the use of high frequency PNP input transistors to produce amplifiers exhibiting low input offset voltage, noise and distortion. In addition, the amplifier provides high output current drive capability while consuming only 420  $\mu\text{A}$  of drain current per amplifier. The NPN output stage used, exhibits no deadband crossover distortion, large output voltage swing, excellent phase and gain margins, low open-loop high frequency output impedance, symmetrical source and sink AC frequency performance.

The MC33178/9 family offers both dual and quad amplifier versions in several package options.

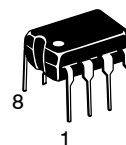
### Features

- 600  $\Omega$  Output Drive Capability
- Large Output Voltage Swing
- Low Offset Voltage: 0.15 mV (Mean)
- Low T.C. of Input Offset Voltage: 2.0  $\mu\text{V}/^\circ\text{C}$
- Low Total Harmonic Distortion: 0.0024% (@ 1.0 kHz w/600  $\Omega$  Load)
- High Gain Bandwidth: 5.0 MHz
- High Slew Rate: 2.0 V/ $\mu\text{s}$
- Dual Supply Operation:  $\pm 2.0$  V to  $\pm 18$  V
- ESD Clamps on the Inputs Increase Ruggedness without Affecting Device Performance



**Figure 1. Representative Schematic Diagram**  
(Each Amplifier)

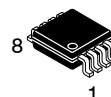
### DUAL



PDIP-8  
P SUFFIX  
CASE 626

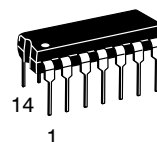


SOIC-8  
D SUFFIX  
CASE 751

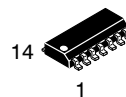


Micro8  
DM SUFFIX  
CASE 846A

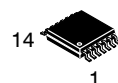
### QUAD



PDIP-14  
P SUFFIX  
CASE 646



SOIC-14  
D SUFFIX  
CASE 751A



TSSOP-14  
DTB SUFFIX  
CASE 948G

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

### DEVICE MARKING INFORMATION

See general marking information in the device marking section on page 3 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 3.

# MC33178, MC33179

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Supply Voltage ( $V_{CC}$ to $V_{EE}$ )	$V_S$	+36	V
Input Differential Voltage Range	$V_{IDR}$	Note 1	V
Input Voltage Range	$V_{IR}$	Note 1	V
Output Short Circuit Duration (Note 2)	$t_{SC}$	Indefinite	sec
Maximum Junction Temperature	$T_J$	+150	°C
Storage Temperature Range	$T_{stg}$	–60 to +150	°C
Maximum Power Dissipation	$P_D$	Note 2	mW
Operating Temperature Range	$T_A$	–40 to +85	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Either or both input voltages should not exceed  $V_{CC}$  or  $V_{EE}$ .

2. Power dissipation must be considered to ensure maximum junction temperature ( $T_J$ ) is not exceeded. (See power dissipation performance characteristic, Figure 2.)

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MC33178DR2G	SOIC–8 (Pb–Free)	2500 / Tape & Reel
MC33178DMR2G	Micro8 (Pb–Free)	4000 / Tape & Reel
MC33179DR2G	SOIC–14 (Pb–Free)	2500 / Tape & Reel
MC33179DTBR2G	TSSOP–14 (Pb–Free)	2500 / Tape & Reel

## DISCONTINUED (Note 3)

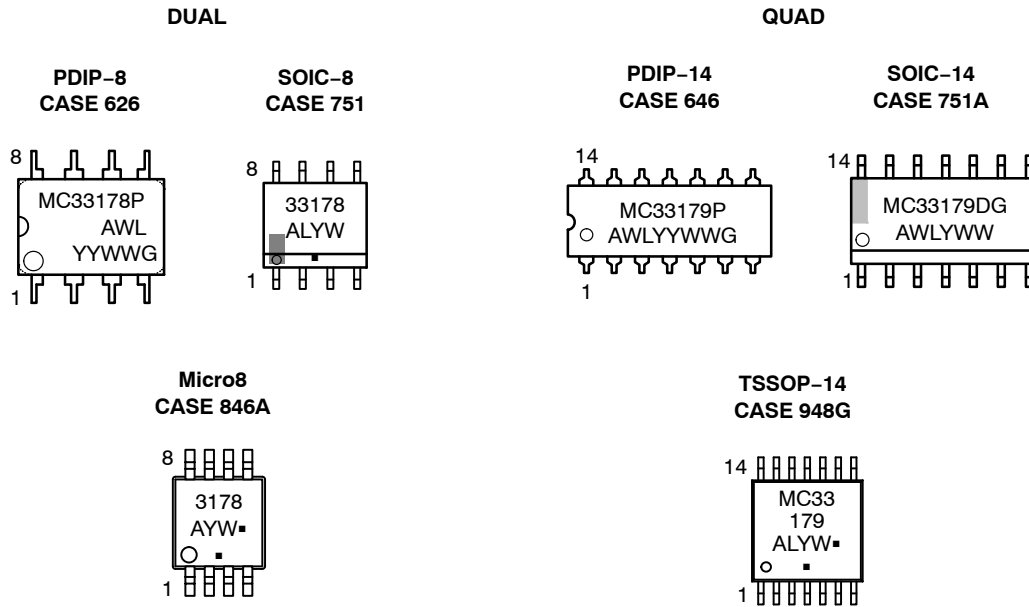
MC33178D	SOIC–8	98 Units / Rail
MC33178DG	SOIC–8 (Pb–Free)	
MC33178DR2	SOIC–8	2500 / Tape & Reel
MC33178P	PDIP–8	50 Units / Rail
MC33178PG	PDIP–8 (Pb–Free)	
MC33178DMR2	Micro8	4000 / Tape & Reel
MC33179D	SOIC–14	55 Units / Rail
MC33179DG	SOIC–14 (Pb–Free)	
MC33179DR2	SOIC–14	2500 / Tape & Reel
MC33179P	PDIP–14	25 Units / Rail
MC33179PG	PDIP–14 (Pb–Free)	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

3. **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on [www.onsemi.com](http://www.onsemi.com).

# MC33178, MC33179

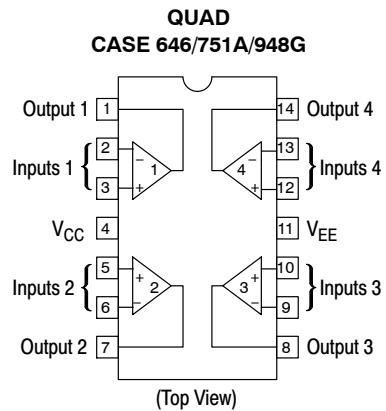
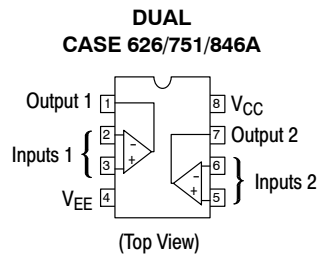
## MARKING DIAGRAMS



A = Assembly Location  
 WL, L = Wafer Lot  
 YY, Y = Year  
 WW, W = Work Week  
 G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

## PIN CONNECTIONS



# MC33178, MC33179

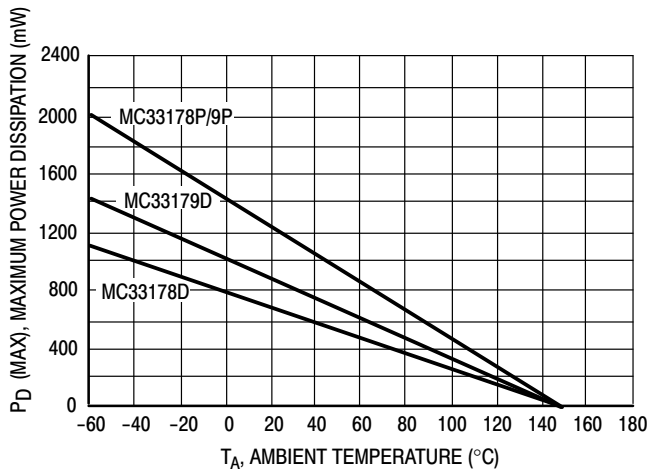
## DC ELECTRICAL CHARACTERISTICS ( $V_{CC} = +15\text{ V}$ , $V_{EE} = -15\text{ V}$ , $T_A = 25^\circ\text{C}$ , unless otherwise noted.)

Characteristics	Figure	Symbol	Min	Typ	Max	Unit
Input Offset Voltage ( $R_S = 50\ \Omega$ , $V_{CM} = 0\text{ V}$ , $V_O = 0\text{ V}$ ) ( $V_{CC} = +2.5\text{ V}$ , $V_{EE} = -2.5\text{ V}$ to $V_{CC} = +15\text{ V}$ , $V_{EE} = -15\text{ V}$ ) $T_A = +25^\circ\text{C}$ $T_A = -40^\circ$ to $+85^\circ\text{C}$	3	$ V_{IO} $	– –	0.15 –	3.0 4.0	mV
Average Temperature Coefficient of Input Offset Voltage ( $R_S = 50\ \Omega$ , $V_{CM} = 0\text{ V}$ , $V_O = 0\text{ V}$ ) $T_A = -40^\circ$ to $+85^\circ\text{C}$	3	$\Delta V_{IO}/\Delta T$	–	2.0	–	$\mu\text{V}/^\circ\text{C}$
Input Bias Current ( $V_{CM} = 0\text{ V}$ , $V_O = 0\text{ V}$ ) $T_A = +25^\circ\text{C}$ $T_A = -40^\circ$ to $+85^\circ\text{C}$	4, 5	$I_{IB}$	– –	100 –	500 600	nA
Input Offset Current ( $V_{CM} = 0\text{ V}$ , $V_O = 0\text{ V}$ ) $T_A = +25^\circ\text{C}$ $T_A = -40^\circ$ to $+85^\circ\text{C}$		$ I_{IO} $	– –	5.0 –	50 60	nA
Common Mode Input Voltage Range ( $\Delta V_{IO} = 5.0\text{ mV}$ , $V_O = 0\text{ V}$ )	6	$V_{ICR}$	–13 –	–14 +14	– +13	V
Large Signal Voltage Gain ( $V_O = -10\text{ V}$ to $+10\text{ V}$ , $R_L = 600\ \Omega$ ) $T_A = +25^\circ\text{C}$ $T_A = -40^\circ$ to $+85^\circ\text{C}$	7, 8	$A_{VOL}$	50 25	200 –	– –	kV/V
Output Voltage Swing ( $V_{ID} = \pm 1.0\text{ V}$ ) ( $V_{CC} = +15\text{ V}$ , $V_{EE} = -15\text{ V}$ ) $R_L = 300\ \Omega$ $R_L = 300\ \Omega$ $R_L = 600\ \Omega$ $R_L = 600\ \Omega$ $R_L = 2.0\text{ k}\Omega$ $R_L = 2.0\text{ k}\Omega$ ( $V_{CC} = +2.5\text{ V}$ , $V_{EE} = -2.5\text{ V}$ ) $R_L = 600\ \Omega$ $R_L = 600\ \Omega$	9, 10, 11	$V_{O+}$ $V_{O-}$ $V_{O+}$ $V_{O-}$ $V_{O+}$ $V_{O-}$ $V_{O+}$ $V_{O-}$	– – +12 – +13 – 1.1 –	+12 –12 +13.6 –13 +14 –13.8 1.6 –1.6	– – – –12 – –13 – –1.1	V
Common Mode Rejection ( $V_{in} = \pm 13\text{ V}$ )	12	CMR	80	110	–	dB
Power Supply Rejection $V_{CC}/V_{EE} = +15\text{ V}/-15\text{ V}$ , $+5.0\text{ V}/-15\text{ V}$ , $+15\text{ V}/-5.0\text{ V}$	13	PSR	80	110	–	dB
Output Short Circuit Current ( $V_{ID} = \pm 1.0\text{ V}$ , Output to Ground) Source ( $V_{CC} = 2.5\text{ V}$ to $15\text{ V}$ ) Sink ( $V_{EE} = -2.5\text{ V}$ to $-15\text{ V}$ )	14, 15	$I_{SC}$	+50 –50	+80 –100	– –	mA
Power Supply Current ( $V_O = 0\text{ V}$ ) ( $V_{CC} = 2.5\text{ V}$ , $V_{EE} = -2.5\text{ V}$ to $V_{CC} = +15\text{ V}$ , $V_{EE} = -15\text{ V}$ ) MC33178 (Dual) $T_A = +25^\circ\text{C}$ $T_A = -40^\circ$ to $+85^\circ\text{C}$ MC33179 (Quad) $T_A = +25^\circ\text{C}$ $T_A = -40^\circ$ to $+85^\circ\text{C}$	16	$I_D$	– – – –	– – 1.7 –	1.4 1.6 2.4 2.6	mA

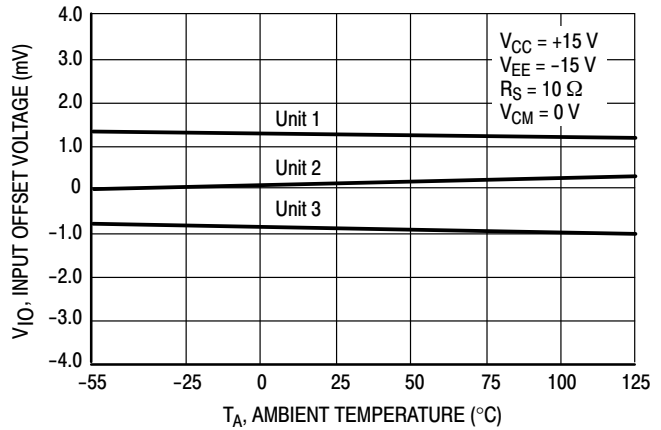
# MC33178, MC33179

**AC ELECTRICAL CHARACTERISTICS** ( $V_{CC} = +15\text{ V}$ ,  $V_{EE} = -15\text{ V}$ ,  $T_A = 25^\circ\text{C}$ , unless otherwise noted.)

Characteristics	Figure	Symbol	Min	Typ	Max	Unit
Slew Rate ( $V_{in} = -10\text{ V}$ to $+10\text{ V}$ , $R_L = 2.0\text{ k}\Omega$ , $C_L = 100\text{ pF}$ , $A_V = +1.0\text{ V}$ )	17, 32	SR	1.2	2.0	–	V/ $\mu\text{s}$
Gain Bandwidth Product ( $f = 100\text{ kHz}$ )	18	GBW	2.5	5.0	–	MHz
AC Voltage Gain ( $R_L = 600\text{ }\Omega$ , $V_O = 0\text{ V}$ , $f = 20\text{ kHz}$ )	19, 20	$A_{VO}$	–	50	–	dB
Unity Gain Bandwidth (Open-Loop) ( $R_L = 600\text{ }\Omega$ , $C_L = 0\text{ pF}$ )		BW	–	3.0	–	MHz
Gain Margin ( $R_L = 600\text{ }\Omega$ , $C_L = 0\text{ pF}$ )	21, 23, 24	$A_m$	–	15	–	dB
Phase Margin ( $R_L = 600\text{ }\Omega$ , $C_L = 0\text{ pF}$ )	22, 23, 24	$\phi_m$	–	60	–	Deg
Channel Separation ( $f = 100\text{ Hz}$ to $20\text{ kHz}$ )	25	CS	–	-120	–	dB
Power Bandwidth ( $V_O = 20\text{ V}_{pp}$ , $R_L = 600\text{ }\Omega$ , $\text{THD} \leq 1.0\%$ )		$\text{BW}_p$	–	32	–	kHz
Total Harmonic Distortion ( $R_L = 600\text{ }\Omega$ , $V_O = 2.0\text{ V}_{pp}$ , $A_V = +1.0\text{ V}$ ) ( $f = 1.0\text{ kHz}$ ) ( $f = 10\text{ kHz}$ ) ( $f = 20\text{ kHz}$ )	26	THD	– – –	0.0024 0.014 0.024	– – –	%
Open Loop Output Impedance ( $V_O = 0\text{ V}$ , $f = 3.0\text{ MHz}$ , $A_V = 10\text{ V}$ )	27	$ Z_O $	–	150	–	$\Omega$
Differential Input Resistance ( $V_{CM} = 0\text{ V}$ )		$R_{in}$	–	200	–	k $\Omega$
Differential Input Capacitance ( $V_{CM} = 0\text{ V}$ )		$C_{in}$	–	10	–	pF
Equivalent Input Noise Voltage ( $R_S = 100\text{ }\Omega$ ) $f = 10\text{ Hz}$ $f = 1.0\text{ kHz}$	28	$e_n$	– –	8.0 7.5	– –	nV/ $\sqrt{\text{Hz}}$
Equivalent Input Noise Current $f = 10\text{ Hz}$ $f = 1.0\text{ kHz}$	29	$i_n$	– –	0.33 0.15	– –	pA/ $\sqrt{\text{Hz}}$

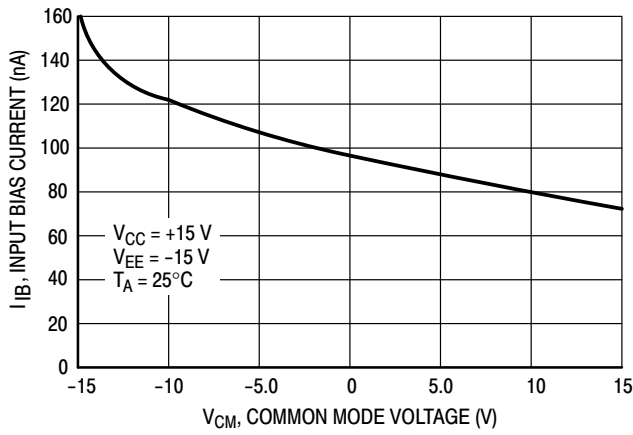


**Figure 2. Maximum Power Dissipation versus Temperature**

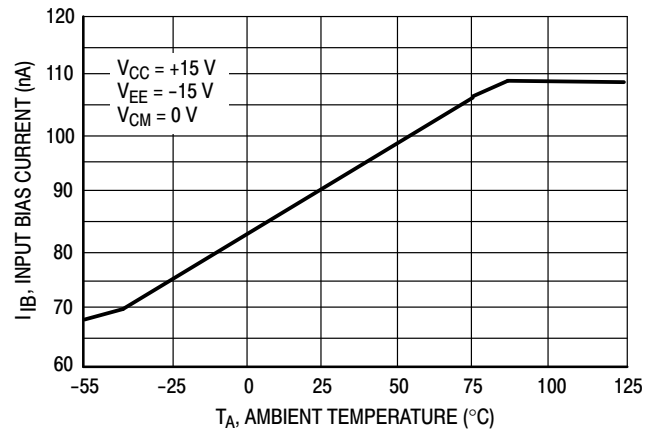


**Figure 3. Input Offset Voltage versus Temperature for 3 Typical Units**

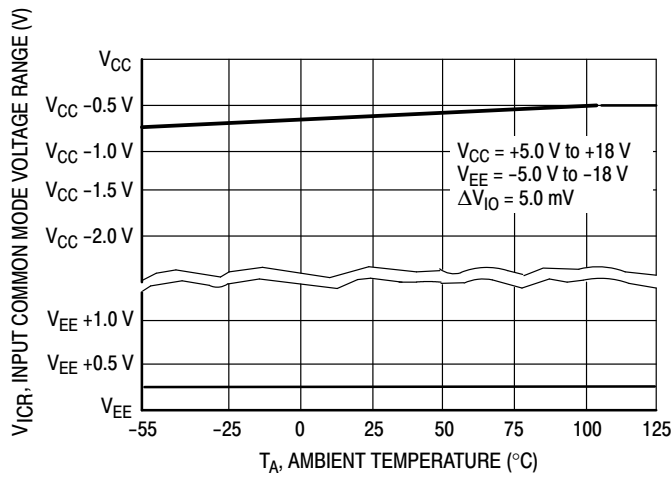
# MC33178, MC33179



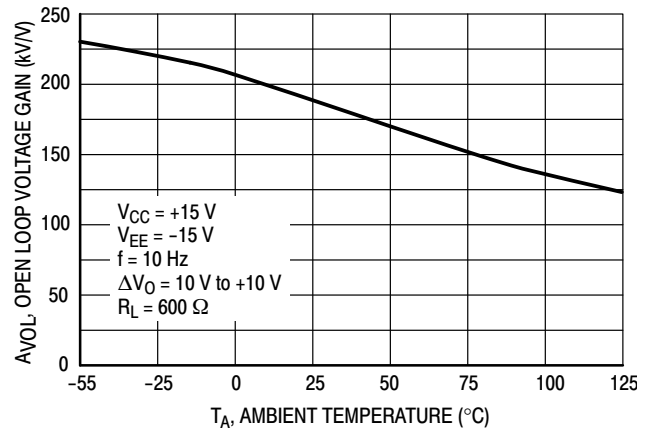
**Figure 4. Input Bias Current versus Common Mode Voltage**



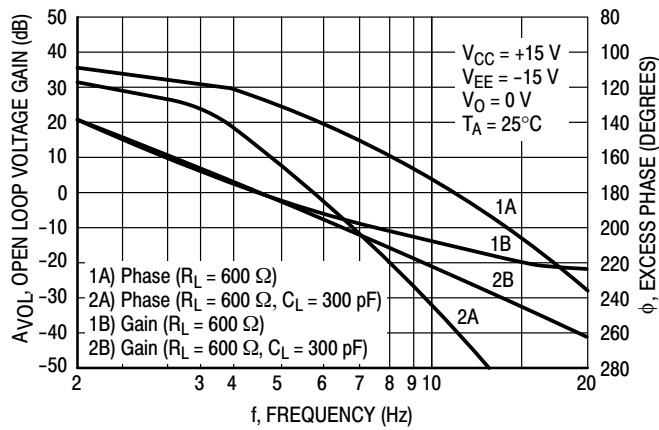
**Figure 5. Input Bias Current versus Temperature**



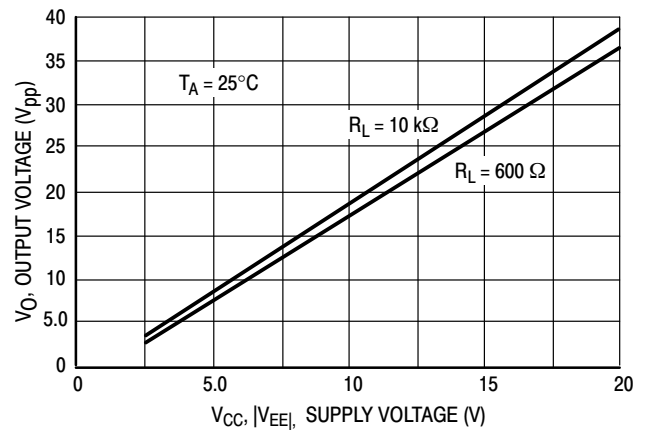
**Figure 6. Input Common Mode Voltage Range versus Temperature**



**Figure 7. Open Loop Voltage Gain versus Temperature**



**Figure 8. Voltage Gain and Phase versus Frequency**



**Figure 9. Output Voltage Swing versus Supply Voltage**

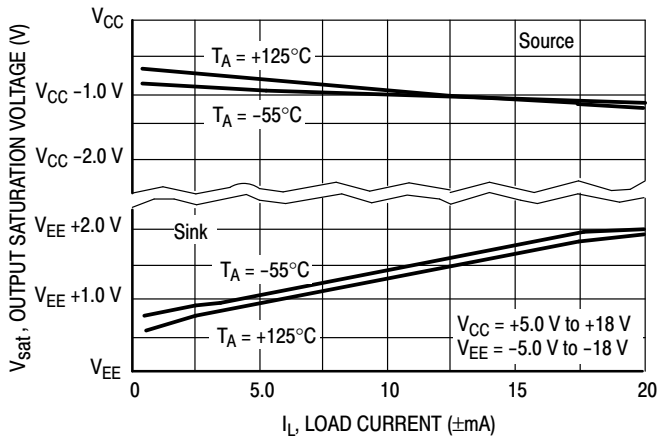


Figure 10. Output Saturation Voltage versus Load Current

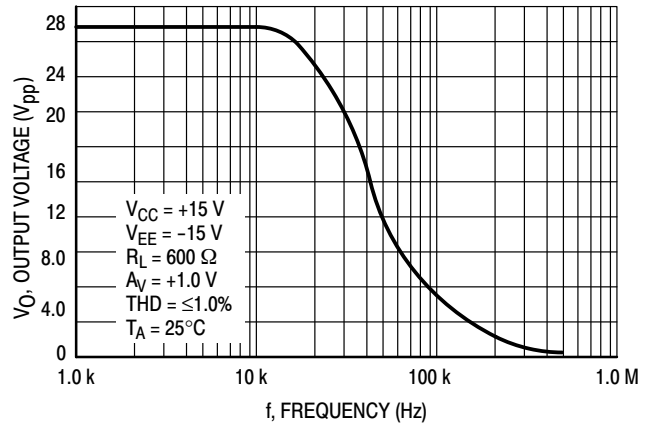


Figure 11. Output Voltage versus Frequency

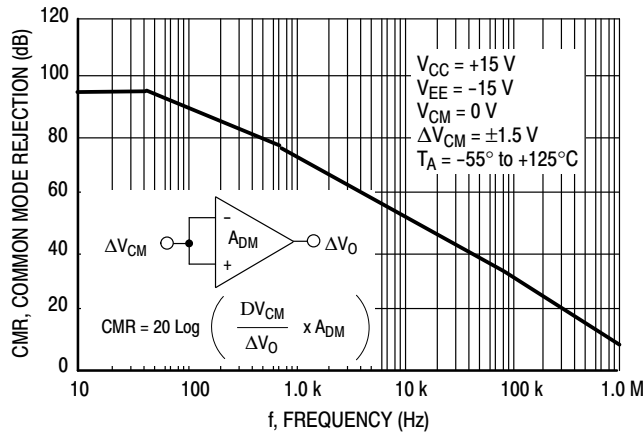


Figure 12. Common Mode Rejection versus Frequency Over Temperature

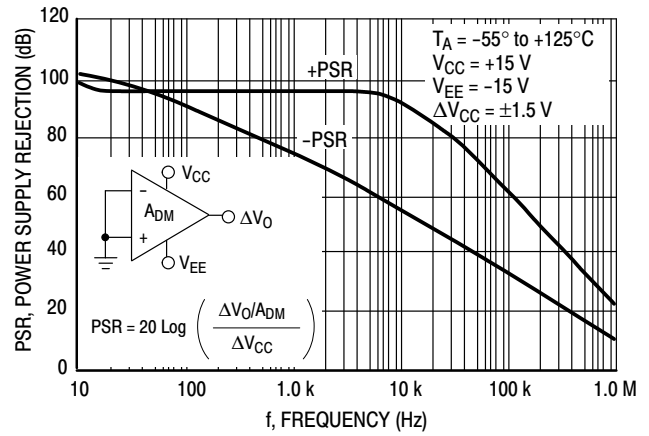


Figure 13. Power Supply Rejection versus Frequency Over Temperature

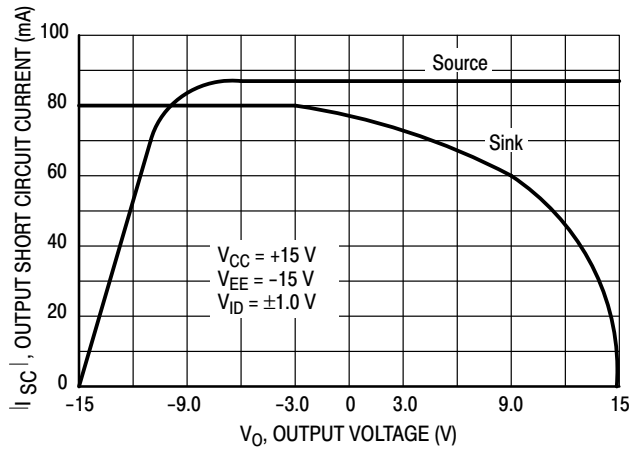


Figure 14. Output Short Circuit Current versus Output Voltage

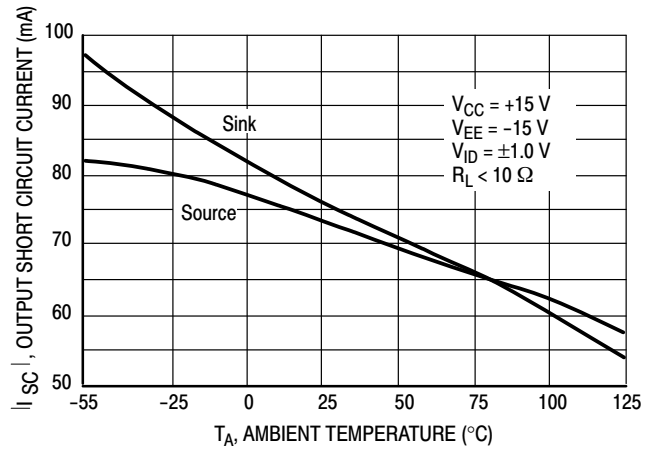


Figure 15. Output Short Circuit Current versus Temperature

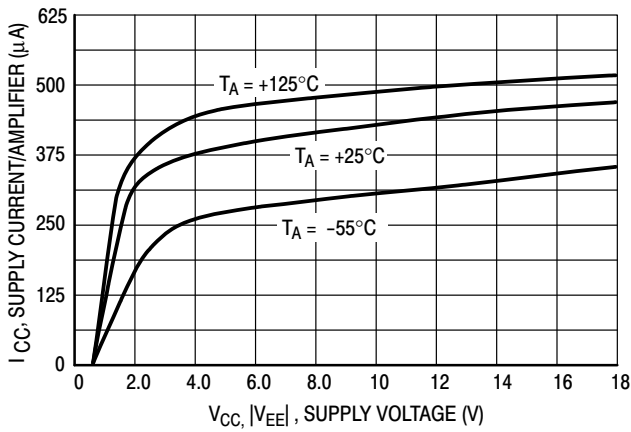


Figure 16. Supply Current versus Supply Voltage with No Load

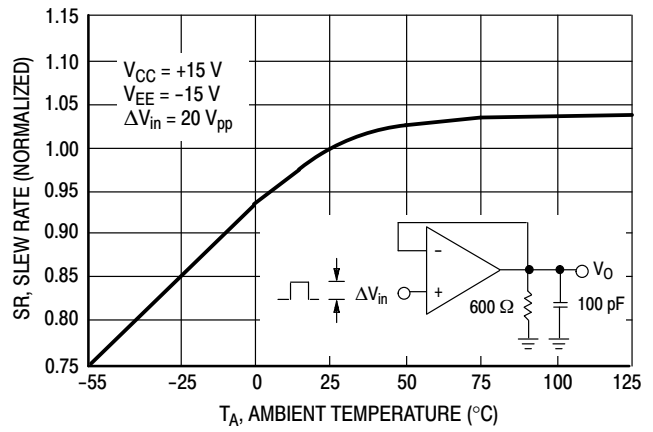


Figure 17. Normalized Slew Rate versus Temperature

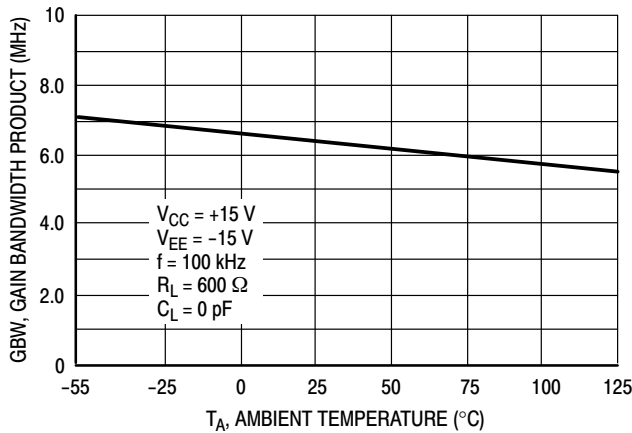


Figure 18. Gain Bandwidth Product versus Temperature

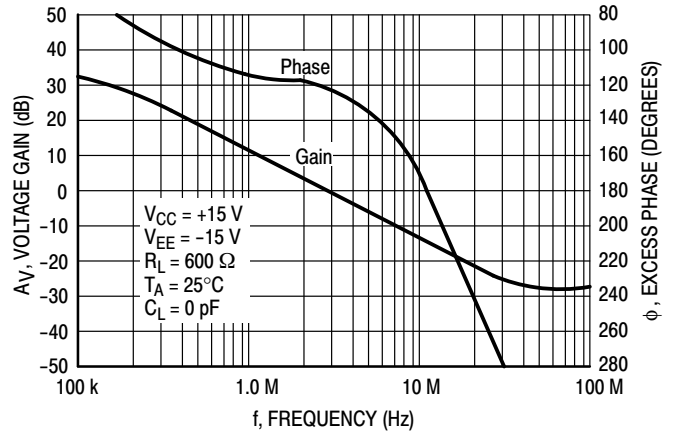


Figure 19. Voltage Gain and Phase versus Frequency

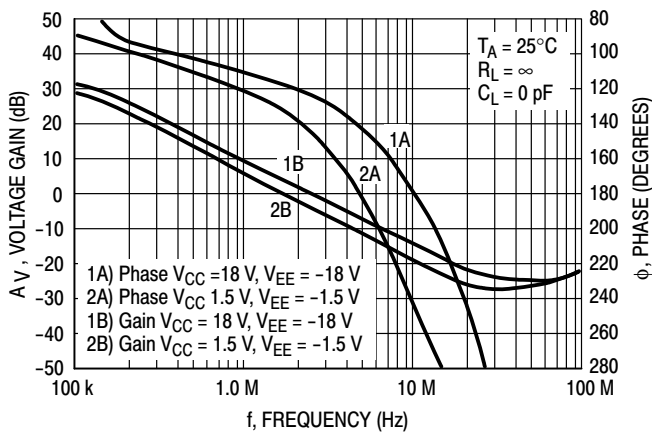


Figure 20. Voltage Gain and Phase versus Frequency

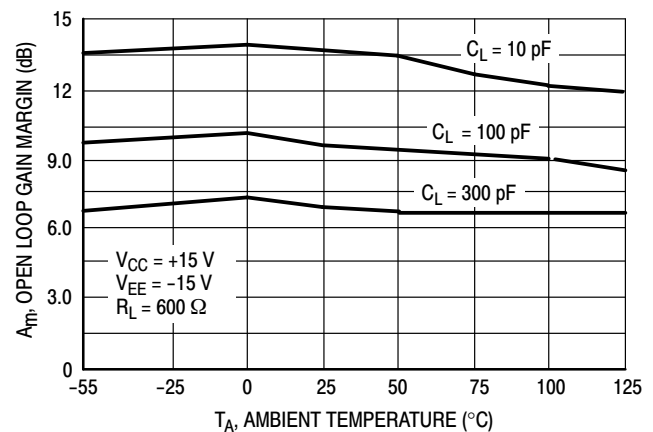
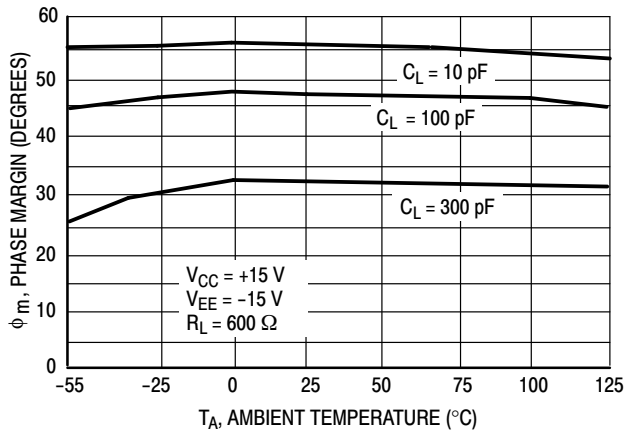
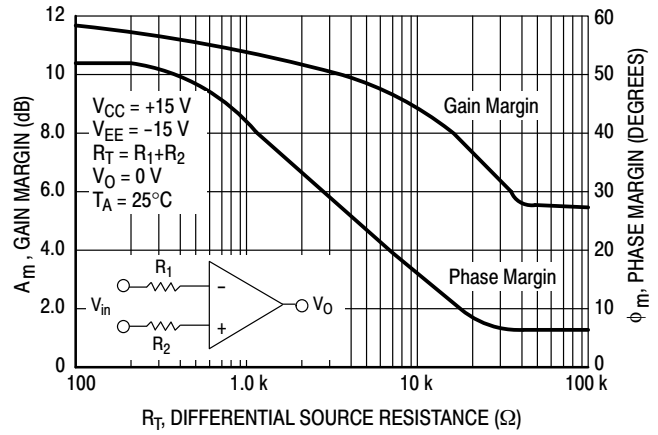


Figure 21. Open Loop Gain Margin versus Temperature

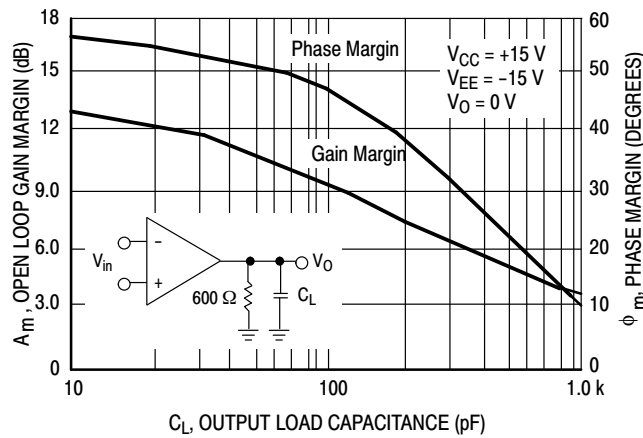




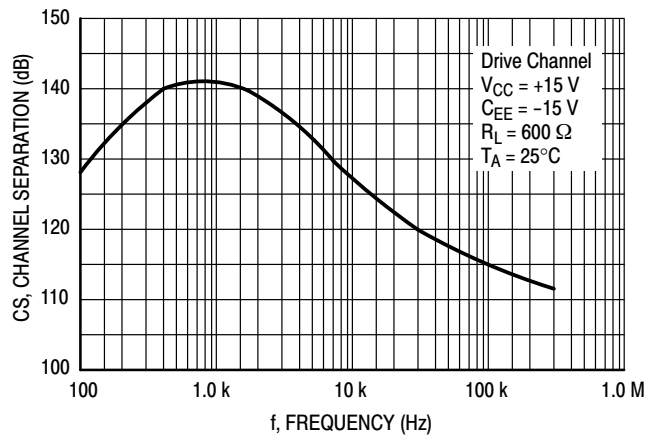
**Figure 22. Phase Margin versus Temperature**



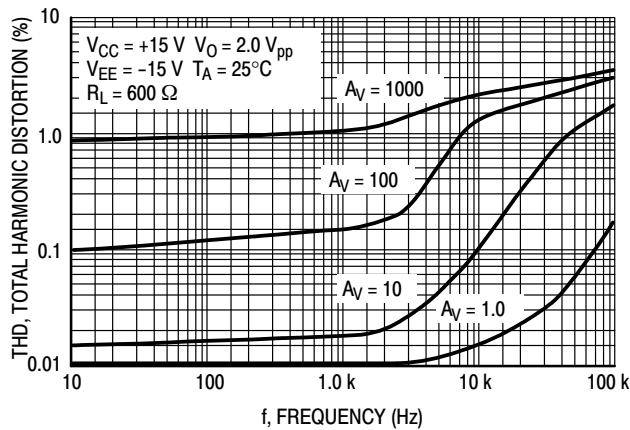
**Figure 23. Phase Margin and Gain Margin versus Differential Source Resistance**



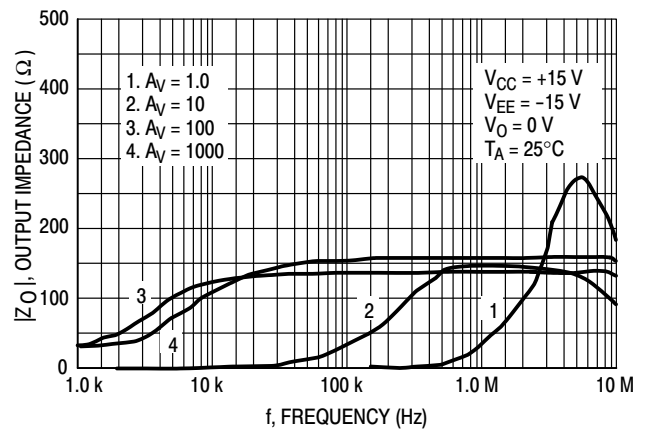
**Figure 24. Open Loop Gain Margin and Phase Margin versus Output Load Capacitance**



**Figure 25. Channel Separation versus Frequency**



**Figure 26. Total Harmonic Distortion versus Frequency**



**Figure 27. Output Impedance versus Frequency**

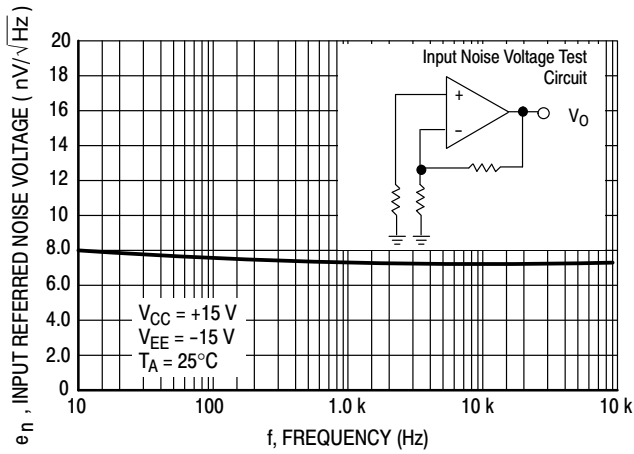


Figure 28. Input Referred Noise Voltage versus Frequency

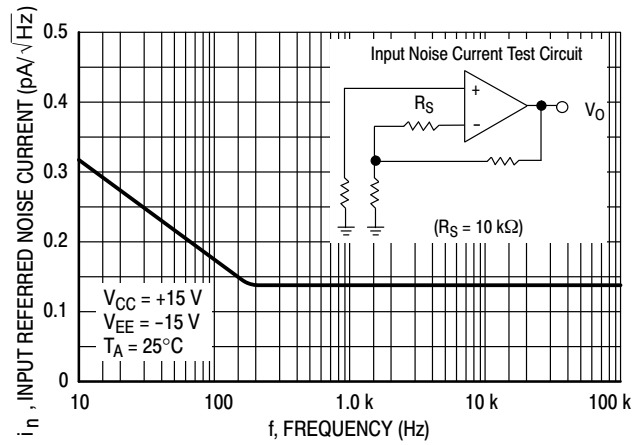


Figure 29. Input Referred Noise Current versus Frequency

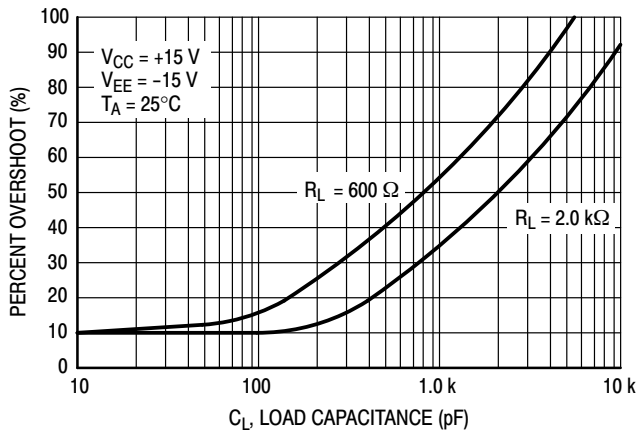


Figure 30. Percent Overshoot versus Load Capacitance

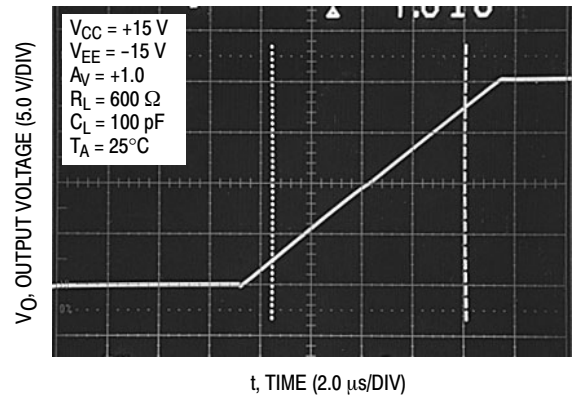


Figure 31. Non-inverting Amplifier Slew Rate

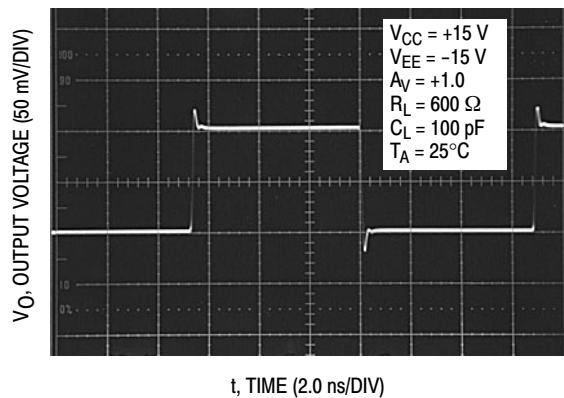


Figure 32. Small Signal Transient Response

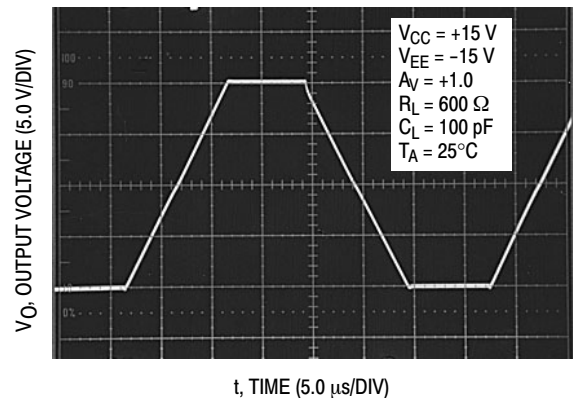
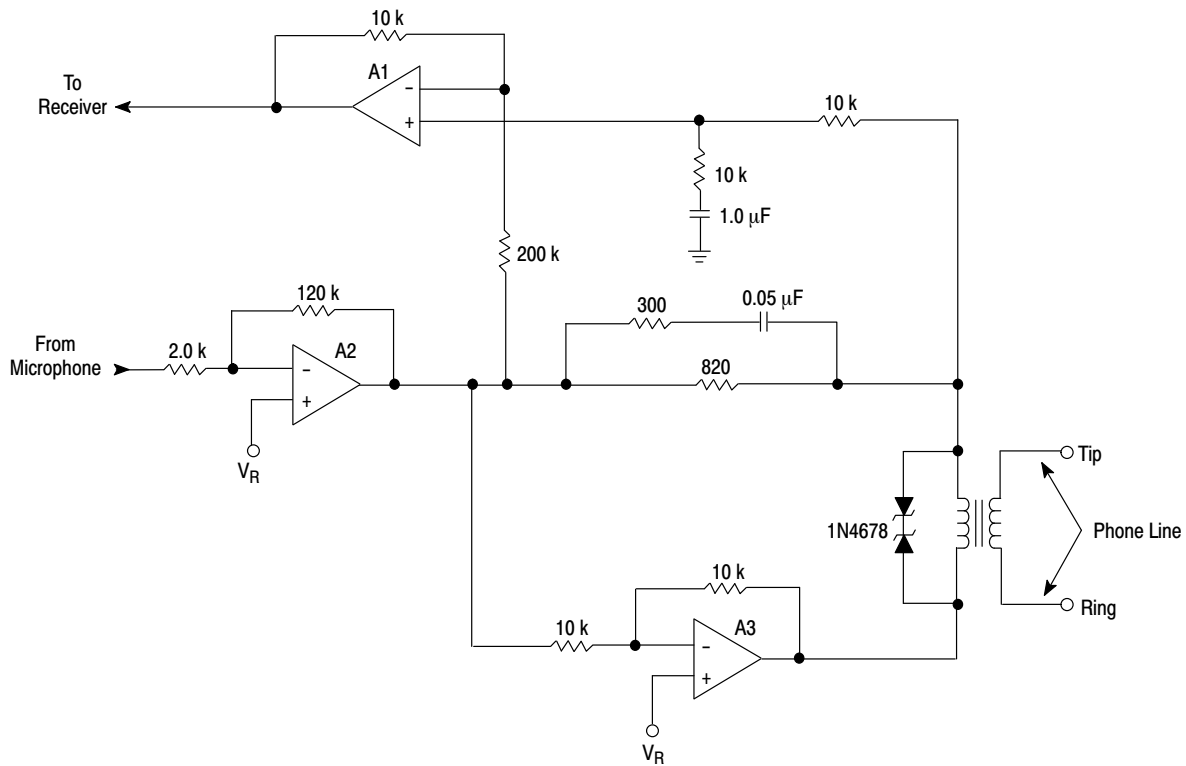


Figure 33. Large Signal Transient Response

## MC33178, MC33179



**Figure 34. Telephone Line Interface Circuit**

## APPLICATION INFORMATION

This unique device uses a boosted output stage to combine a high output current with a drain current lower than similar bipolar input op amps. Its 60° phase margin and 15 dB gain margin ensure stability with up to 1000 pF of load capacitance (see Figure 24). The ability to drive a minimum 600 Ω load makes it particularly suitable for telecom applications. Note that in the sample circuit in Figure 34 both A2 and A3 are driving equivalent loads of approximately 600 Ω.

The low input offset voltage and moderately high slew rate and gain bandwidth product make it attractive for a variety of other applications. For example, although it is not single supply (the common mode input range does not include ground), it is specified at +5.0 V with a typical common mode rejection of 110 dB. This makes it an excellent choice for use with digital circuits. The high common mode rejection, which is stable over temperature, coupled with a low noise figure and low distortion, is an ideal op amp for audio circuits.

The output stage of the op amp is current limited and therefore has a certain amount of protection in the event of a short circuit. However, because of its high current output, it is especially important not to allow the device to exceed the maximum junction temperature, particularly with the

MC33179 (quad op amp). Shorting more than one amplifier could easily exceed the junction temperature to the extent of causing permanent damage.

### Stability

As usual with most high frequency amplifiers, proper lead dress, component placement, and PC board layout should be exercised for optimum frequency performance. For example, long unshielded input or output leads may result in unwanted input/output coupling. In order to preserve the relatively low input capacitance associated with these amplifiers, resistors connected to the inputs should be immediately adjacent to the input pin to minimize additional stray input capacitance. This not only minimizes the input pole frequency for optimum frequency response, but also minimizes extraneous “pick up” at this node. Supplying decoupling with adequate capacitance immediately adjacent to the supply pin is also important, particularly over temperature, since many types of decoupling capacitors exhibit great impedance changes over temperature.

Additional stability problems can be caused by high load capacitances and/or a high source resistance. Simple compensation schemes can be used to alleviate these effects.

If a high source of resistance is used ( $R_1 > 1.0 \text{ k}\Omega$ ), a compensation capacitor equal to or greater than the input capacitance of the op amp (10 pF) placed across the feedback resistor (see Figure 35) can be used to neutralize that pole and prevent outer loop oscillation. Since the closed loop transient response will be a function of that capacitance, it is important to choose the optimum value for that capacitor. This can be determined by the following Equation:

$$C_C = (1 + [R_1/R_2])^2 \times C_L (Z_O/R_2) \quad (1)$$

where:  $Z_O$  is the output impedance of the op amp.

For moderately high capacitive loads ( $500 \text{ pF} < C_L < 1500 \text{ pF}$ ) the addition of a compensation resistor on the order of  $20 \Omega$  between the output and the feedback loop will help to decrease miller loop oscillation (see Figure 36). For high capacitive loads ( $C_L > 1500 \text{ pF}$ ), a combined compensation scheme should be used (see Figure 37). Both the compensation resistor and the compensation capacitor affect the transient response and can be calculated for optimum performance. The value of  $C_C$  can be calculated using Equation 1. The Equation to calculate  $R_C$  is as follows:

$$R_C = Z_O \times R_1/R_2 \quad (2)$$

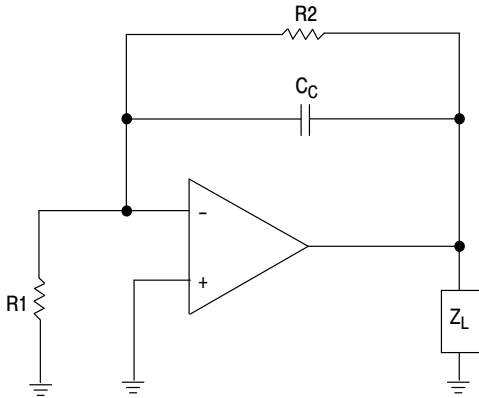


Figure 35. Compensation for High Source Impedance

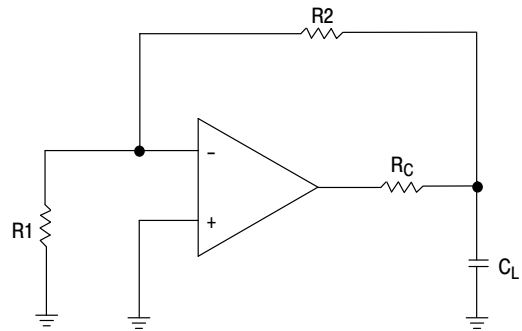


Figure 36. Compensation Circuit for Moderate Capacitive Loads

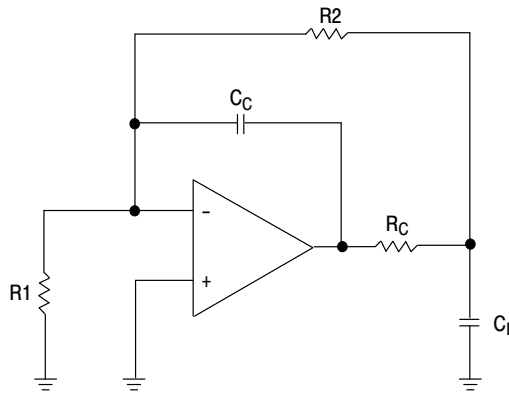
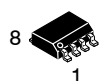


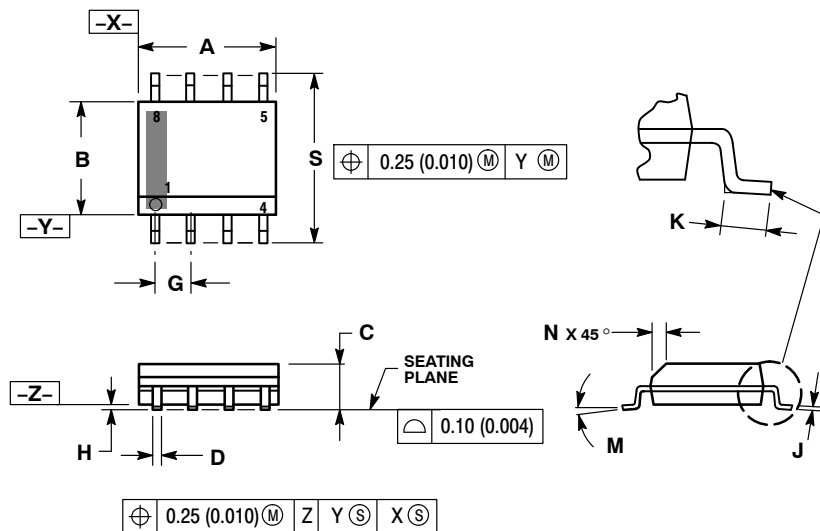
Figure 37. Compensation Circuit for High Capacitive Loads



SCALE 1:1

SOIC-8 NB  
CASE 751-07  
ISSUE AK

DATE 16 FEB 2011

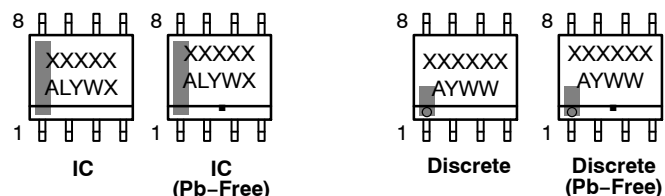
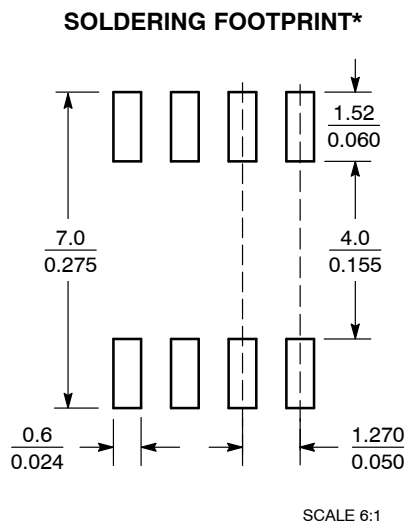


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

GENERIC  
MARKING DIAGRAM\*



XXXXXX = Specific Device Code  
 A = Assembly Location  
 L = Wafer Lot  
 Y = Year  
 W = Work Week  
 ■ = Pb-Free Package

XXXXXX = Specific Device Code  
 A = Assembly Location  
 Y = Year  
 WW = Work Week  
 ■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

\*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOIC-8 NB	PAGE 1 OF 2

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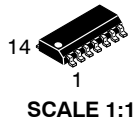
**SOIC-8 NB**  
**CASE 751-07**  
**ISSUE AK**

DATE 16 FEB 2011

<b>STYLE 1:</b> PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	<b>STYLE 2:</b> PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	<b>STYLE 3:</b> PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	<b>STYLE 4:</b> PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
<b>STYLE 5:</b> PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	<b>STYLE 6:</b> PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	<b>STYLE 7:</b> PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	<b>STYLE 8:</b> PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
<b>STYLE 9:</b> PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	<b>STYLE 10:</b> PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	<b>STYLE 11:</b> PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	<b>STYLE 12:</b> PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
<b>STYLE 13:</b> PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	<b>STYLE 14:</b> PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	<b>STYLE 15:</b> PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	<b>STYLE 16:</b> PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
<b>STYLE 17:</b> PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	<b>STYLE 18:</b> PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	<b>STYLE 19:</b> PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	<b>STYLE 20:</b> PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
<b>STYLE 21:</b> PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	<b>STYLE 22:</b> PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	<b>STYLE 23:</b> PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	<b>STYLE 24:</b> PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
<b>STYLE 25:</b> PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	<b>STYLE 26:</b> PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	<b>STYLE 27:</b> PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	<b>STYLE 28:</b> PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
<b>STYLE 29:</b> PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	<b>STYLE 30:</b> PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

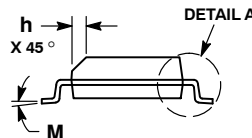
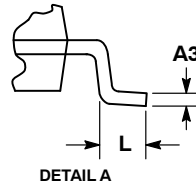
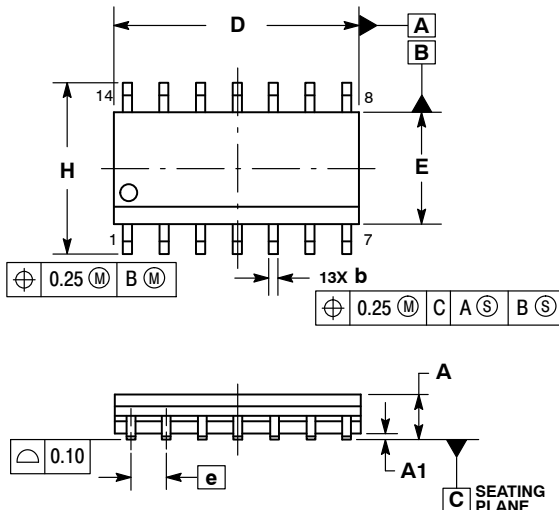
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SOIC-14 NB  
CASE 751A-03  
ISSUE L

DATE 03 FEB 2016

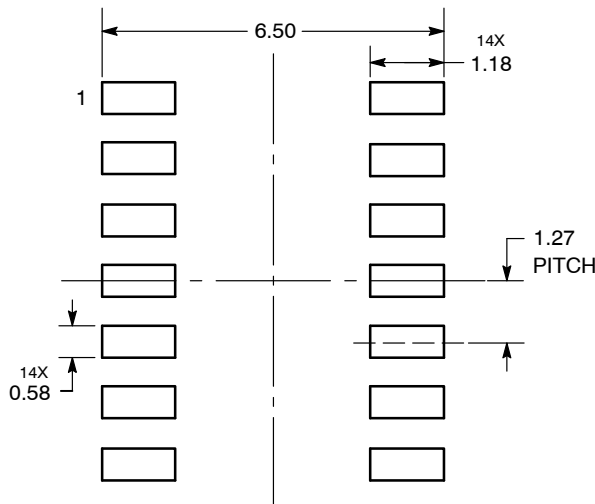


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0°	7°	0°	7°

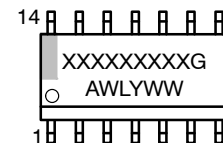
SOLDERING FOOTPRINT\*



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC  
MARKING DIAGRAM\*



XXXXXX = Specific Device Code  
A = Assembly Location  
WL = Wafer Lot  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SOIC-14  
CASE 751A-03  
ISSUE L

DATE 03 FEB 2016

STYLE 1:  
PIN 1. COMMON CATHODE  
2. ANODE/CATHODE  
3. ANODE/CATHODE  
4. NO CONNECTION  
5. ANODE/CATHODE  
6. NO CONNECTION  
7. ANODE/CATHODE  
8. ANODE/CATHODE  
9. ANODE/CATHODE  
10. NO CONNECTION  
11. ANODE/CATHODE  
12. ANODE/CATHODE  
13. NO CONNECTION  
14. COMMON ANODE

STYLE 2:  
CANCELLED

STYLE 3:  
PIN 1. NO CONNECTION  
2. ANODE  
3. ANODE  
4. NO CONNECTION  
5. ANODE  
6. NO CONNECTION  
7. ANODE  
8. ANODE  
9. ANODE  
10. NO CONNECTION  
11. ANODE  
12. ANODE  
13. NO CONNECTION  
14. COMMON CATHODE

STYLE 4:  
PIN 1. NO CONNECTION  
2. CATHODE  
3. CATHODE  
4. NO CONNECTION  
5. CATHODE  
6. NO CONNECTION  
7. CATHODE  
8. CATHODE  
9. CATHODE  
10. NO CONNECTION  
11. CATHODE  
12. CATHODE  
13. NO CONNECTION  
14. COMMON ANODE

STYLE 5:  
PIN 1. COMMON CATHODE  
2. ANODE/CATHODE  
3. ANODE/CATHODE  
4. ANODE/CATHODE  
5. ANODE/CATHODE  
6. NO CONNECTION  
7. COMMON ANODE  
8. COMMON CATHODE  
9. ANODE/CATHODE  
10. ANODE/CATHODE  
11. ANODE/CATHODE  
12. ANODE/CATHODE  
13. NO CONNECTION  
14. COMMON ANODE

STYLE 6:  
PIN 1. CATHODE  
2. CATHODE  
3. CATHODE  
4. CATHODE  
5. CATHODE  
6. CATHODE  
7. CATHODE  
8. ANODE  
9. ANODE  
10. ANODE  
11. ANODE  
12. ANODE  
13. ANODE  
14. ANODE

STYLE 7:  
PIN 1. ANODE/CATHODE  
2. COMMON ANODE  
3. COMMON CATHODE  
4. ANODE/CATHODE  
5. ANODE/CATHODE  
6. ANODE/CATHODE  
7. ANODE/CATHODE  
8. ANODE/CATHODE  
9. ANODE/CATHODE  
10. ANODE/CATHODE  
11. COMMON CATHODE  
12. COMMON ANODE  
13. ANODE/CATHODE  
14. ANODE/CATHODE

STYLE 8:  
PIN 1. COMMON CATHODE  
2. ANODE/CATHODE  
3. ANODE/CATHODE  
4. NO CONNECTION  
5. ANODE/CATHODE  
6. ANODE/CATHODE  
7. COMMON ANODE  
8. COMMON ANODE  
9. ANODE/CATHODE  
10. ANODE/CATHODE  
11. NO CONNECTION  
12. ANODE/CATHODE  
13. ANODE/CATHODE  
14. COMMON CATHODE

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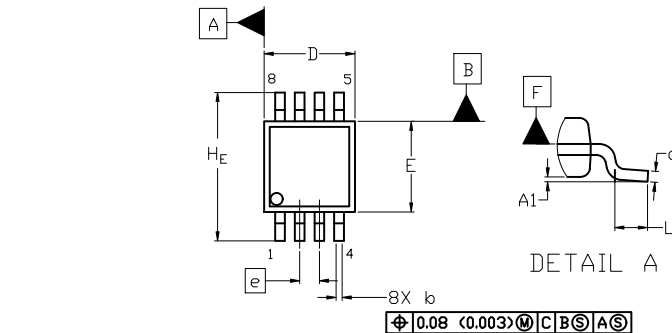




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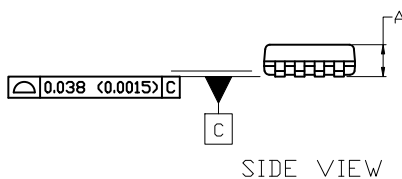
**Micro8**  
**CASE 846A-02**  
**ISSUE K**

DATE 16 JUL 2020

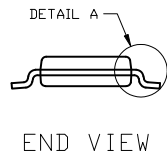


TOP VIEW

NOTE 3



SIDE VIEW

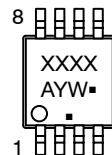


END VIEW

**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION E DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS D AND E ARE DETERMINED AT DATUM F.
5. DATUMS A AND B ARE TO BE DETERMINED AT DATUM F.
6. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.10
A1	0.05	0.08	0.15
b	0.25	0.33	0.40
c	0.13	0.18	0.23
D	2.90	3.00	3.10
E	2.90	3.00	3.10
e	0.65 BSC		
H <sub>E</sub>	4.75	4.90	5.05
L	0.40	0.55	0.70

**GENERIC**  
**MARKING DIAGRAM\***


XXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
W = Work Week  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

**RECOMMENDED**  
**MOUNTING FOOTPRINT**

■ For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM-10.

**STYLE 1:**

- PIN 1. SOURCE
- SOURCE
- SOURCE
- GATE
- DRAIN
- DRAIN
- DRAIN
- DRAIN

**STYLE 2:**

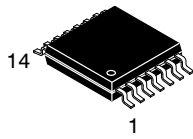
- PIN 1. SOURCE 1
- GATE 1
- SOURCE 2
- GATE 2
- DRAIN 2
- DRAIN 2
- DRAIN 1
- DRAIN 1

**STYLE 3:**

- PIN 1. N-SOURCE
- N-GATE
- P-SOURCE
- P-GATE
- P-DRAIN
- P-DRAIN
- N-DRAIN
- N-DRAIN

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<b>DESCRIPTION:</b>	<b>MICRO8</b>	<b>PAGE 1 OF 1</b>

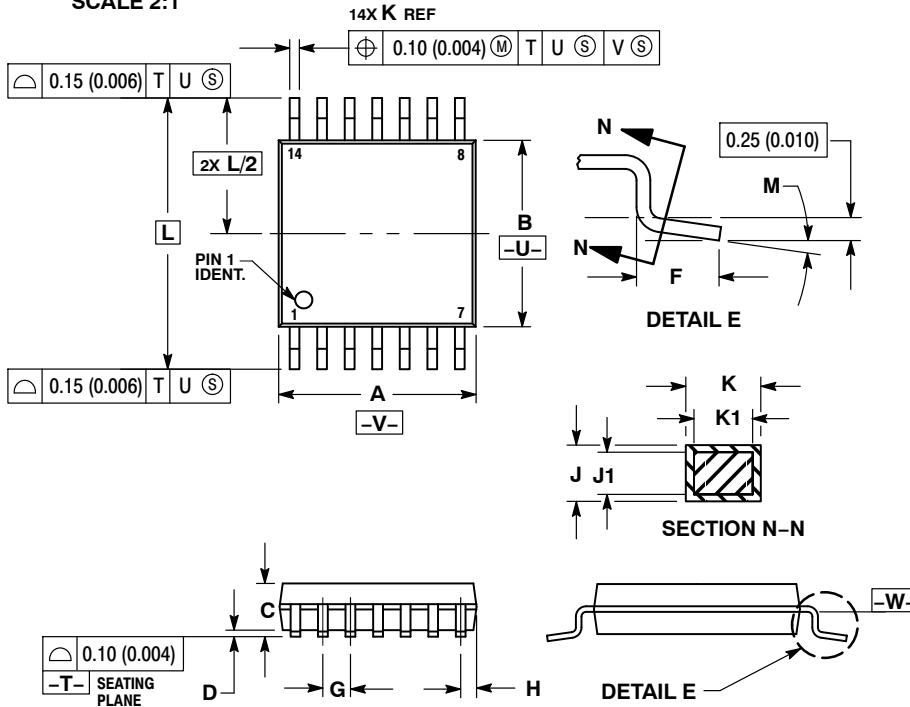
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CASE 948G  
ISSUE C

DATE 17 FEB 2016

SCALE 2:1

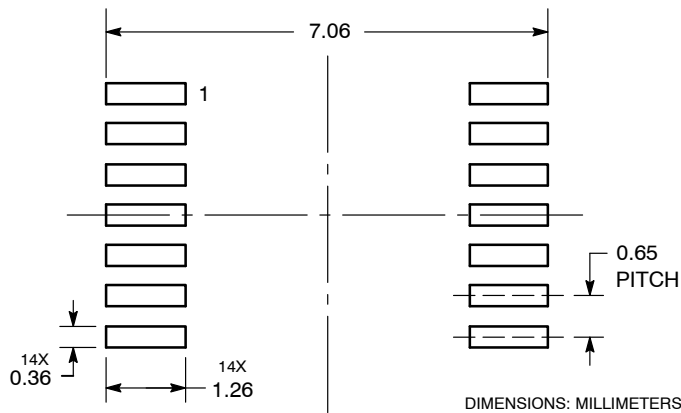


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

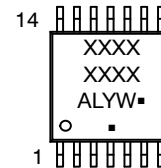
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

RECOMMENDED  
SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC  
MARKING DIAGRAM\*



A = Assembly Location  
L = Wafer Lot  
Y = Year  
W = Work Week  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	TSSOP-14 WB	PAGE 1 OF 1

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